# NVMFD5853NL

# Power MOSFET

## 40 V, 10 mΩ, 34 A, Dual N−Channel Logic Level, Dual SO−8FL

**Features**

- Small Footprint (5x6 mm) for Compact Designs
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- NVMFD5853NLWF − Wettable Flanks Option for Enhanced Optical Inspection
- AEC−Q101 Qualified and PPAP Capable
- This is a Pb−Free Device

**MAXIMUM RATINGS** ($T_J$ = 25°C unless otherwise noted)

| Parameter | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain−to−Source Voltage | | | $V_{DSS}$ | 40 | V |
| Gate−to−Source Voltage | | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3, 4) | Steady State | $T_{mb}$ = 25°C | $I_D$ | 34 | A |
| | | $T_{mb}$ = 100°C | | 24 | |
| Power Dissipation $R_{\Psi J-mb}$ (Notes 1, 2, 3) | | $T_{mb}$ = 25°C | $P_D$ | 24 | W |
| | | $T_{mb}$ = 100°C | | 12 | |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3 & 4) | Steady State | $T_A$ = 25°C | $I_D$ | 12 | A |
| | | $T_A$ = 100°C | | 8.5 | |
| Power Dissipation $R_{\theta JA}$ (Notes 1 & 3) | | $T_A$ = 25°C | $P_D$ | 3.0 | W |
| | | $T_A$ = 100°C | | 1.5 | |
| Pulsed Drain Current | $T_A$ = 25°C, $t_p$ = 10 μs | | $I_{DM}$ | 165 | A |
| Operating Junction and Storage Temperature | | | $T_J$, $T_{stg}$ | −55 to 175 | °C |
| Source Current (Body Diode) | | | $I_S$ | 34 | A |
| Single Pulse Drain−to−Source Avalanche Energy ($T_J$ = 25°C, $V_{GS}$ = 10 V, $I_{L(pk)}$ = 28.3 A, L = 0.1 mH, $R_G$ = 25 Ω) | | | $E_{AS}$ | 40 | mJ |
| Lead Temperature for Soldering Purposes (1/8″ from case for 10 s) | | | $T_L$ | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**THERMAL RESISTANCE MAXIMUM RATINGS** (Note 1)

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Junction−to−Mounting Board (top) − Steady State (Notes 2, 3) | $R_{\Psi J-mb}$ | 6.2 | °C/W |
| Junction−to−Ambient − Steady State (Note 3) | $R_{\theta JA}$ | 51 | |
| Junction−to−Ambient − Steady State (min footprint) | | 162 | |

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51−12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface−mounted on FR4 board using a 650 $mm^2$, 2 oz. Cu pad.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second are higher but are dependent on pulse duration and duty cycle.

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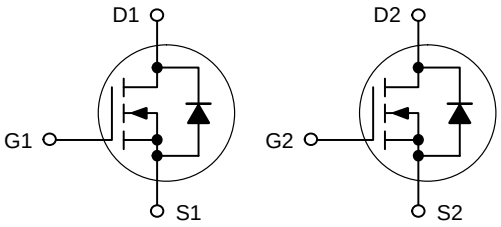
| $V_{(BR)DSS}$ | $R_{DS(on)}$ MAX | $I_D$ MAX |
|---|---|---|
| 40 V | 10 mΩ @ 10 V | 34 A |
| | 15 mΩ @ 4.5 V | |

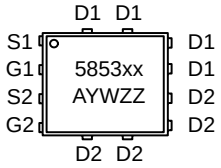
**Dual N−Channel**




1

**DFN8 5x6**
**(SO8FL)**
**CASE 506BT**

**MARKING DIAGRAM**




5853NL = Specific Device Code for NVMFD5853NL
5853LW = Specific Device Code for NVMFD5853NLWF
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

**ORDERING INFORMATION**

| Device | Package | Shipping† |
|---|---|---|
| NVMFD5853NLT1G | DFN8 (Pb−Free) | 1500 / Tape & Reel |
| NVMFD5853NLWFT1G | DFN8 (Pb−Free) | 1500 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain−to−Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | | 40 | | | V |
| Drain−to−Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | | 37.1 | | mV/°C |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 40 V | $T_J$ = 25°C | | | 1.0 | μA |
| | | | $T_J$ = 125°C | | | 100 | |
| Gate−to−Source Leakage Current | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | | ±100 | nA |
| **ON CHARACTERISTICS** (Note 5) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS}$ = $V_{DS}$, $I_D$ = 250 μA | | 1.4 | | 2.4 | V |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | | 5.9 | | mV/°C |
| Drain−to−Source On Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 15 A | | | 8.4 | 10 | mΩ |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 15 A | | | 12.7 | 15 | |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = 5 V, $I_D$ = 5 A | | | 22 | | S |
| **CHARGES AND CAPACITANCES** | | | | | | | |
| Input Capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, f = 1.0 MHz, $V_{DS}$ = 25 V | | | 1100 | | pF |
| Output Capacitance | $C_{oss}$ | | | | 152 | | |
| Reverse Transfer Capacitance | $C_{rss}$ | | | | 100 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 32 V, $I_D$ = 15 A | | | 12.8 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | | 1.0 | | |
| Gate−to−Source Charge | $Q_{GS}$ | | | | 3.7 | | |
| Gate−to−Drain Charge | $Q_{GD}$ | | | | 7.0 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 32 V, $I_D$ = 15 A | | | 23 | | nC |
| **SWITCHING CHARACTERISTICS** (Note 6) | | | | | | | |
| Turn−On Delay Time | $t_{d(on)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 20 V, $I_D$ = 15 A, $R_G$ = 2.5 Ω | | | 10 | | ns |
| Rise Time | $t_r$ | | | | 53 | | |
| Turn−Off Delay Time | $t_{d(off)}$ | | | | 17 | | |
| Fall Time | $t_f$ | | | | 30 | | |
| Turn−On Delay Time | $t_{d(on)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 20 V, $I_D$ = 15 A, $R_G$ = 2.5 Ω | | | 9.0 | | ns |
| Rise Time | $t_r$ | | | | 23 | | |
| Turn−Off Delay Time | $t_{d(off)}$ | | | | 22 | | |
| Fall Time | $t_f$ | | | | 4.3 | | |
| **DRAIN−SOURCE DIODE CHARACTERISTICS** | | | | | | | |
| Forward Diode Voltage | $V_{SD}$ | $V_{GS}$ = 0 V, $I_S$ = 20 A | $T_J$ = 25°C | | 0.84 | 1.1 | V |
| | | | $T_J$ = 125°C | | 0.69 | | |
| Reverse Recovery Time | $t_{RR}$ | $V_{GS}$ = 0 V, $d_{IS}/d_t$ = 100 A/μs, $I_S$ = 15 A | | | 20 | | ns |
| Charge Time | $t_a$ | | | | 12 | | |
| Discharge Time | $t_b$ | | | | 8.1 | | |
| Reverse Recovery Charge | $Q_{RR}$ | | | | 12.1 | | nC |

5. Pulse Test: pulse width = 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

## TYPICAL CHARACTERISTICS

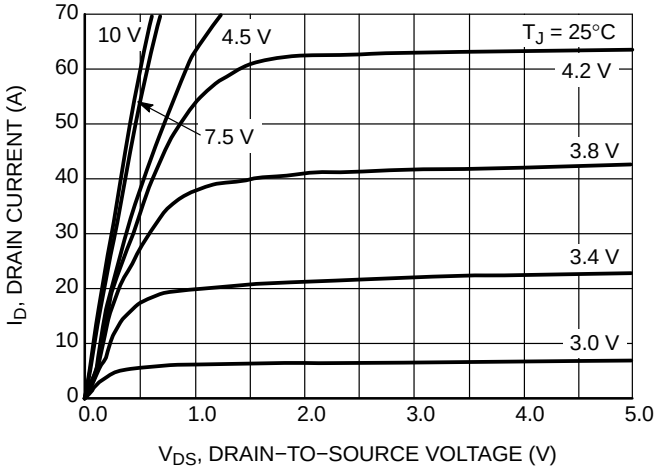



**Figure 1. On−Region Characteristics**

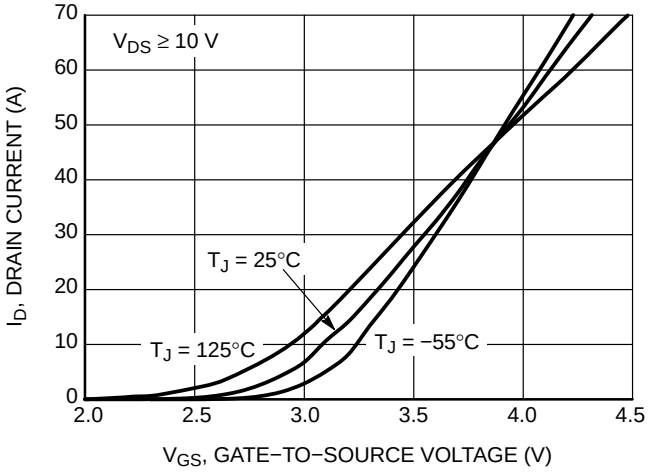



**Figure 2. Transfer Characteristics**

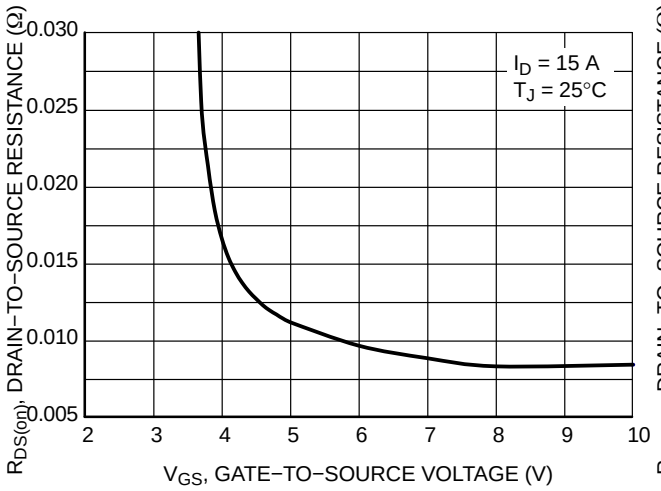



**Figure 3. On−Resistance vs. $V_{GS}$**

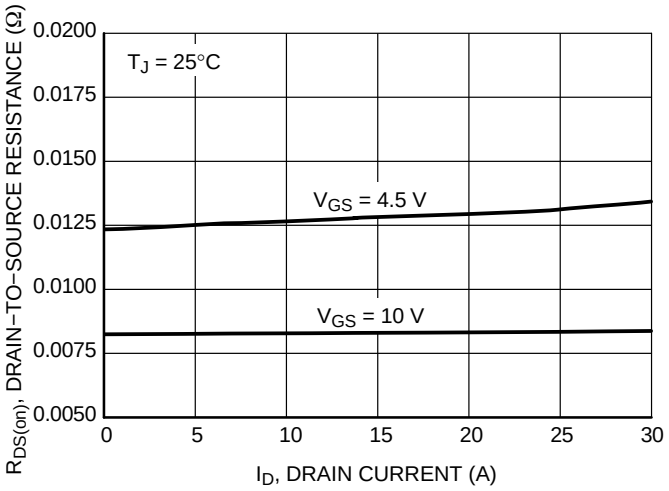



**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**

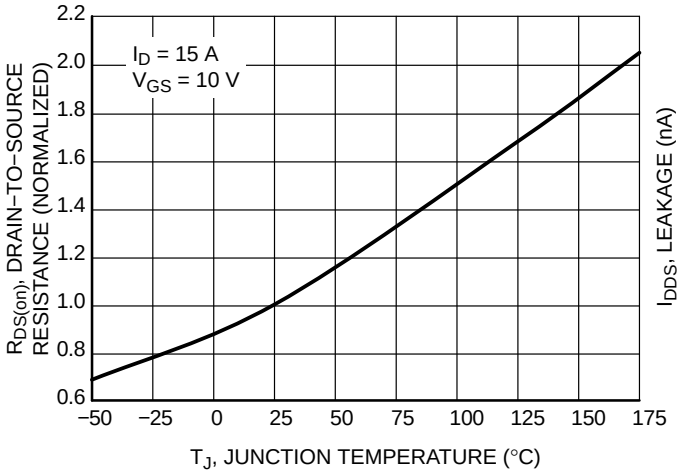



**Figure 5. On−Resistance Variation with Temperature**

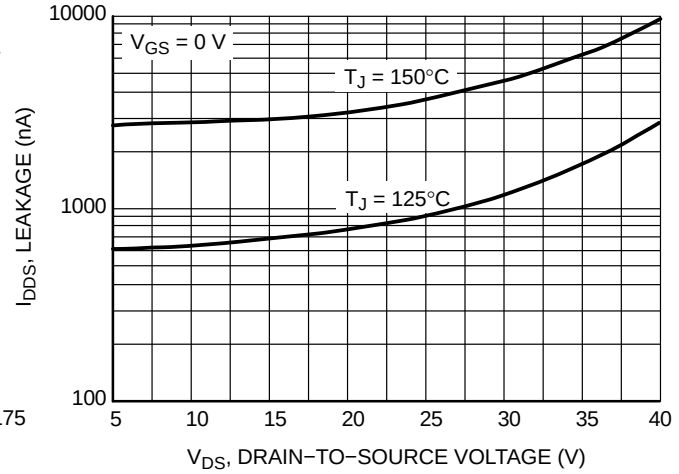



**Figure 6. Drain−to−Source Leakage Current vs. Voltage**

## TYPICAL CHARACTERISTICS

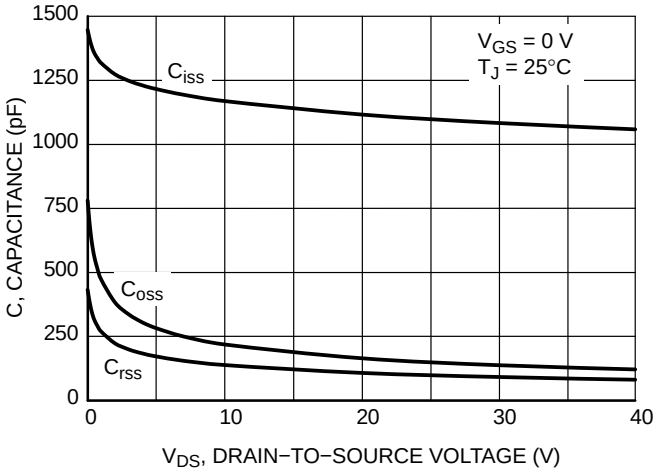



**Figure 7. Capacitance Variation**

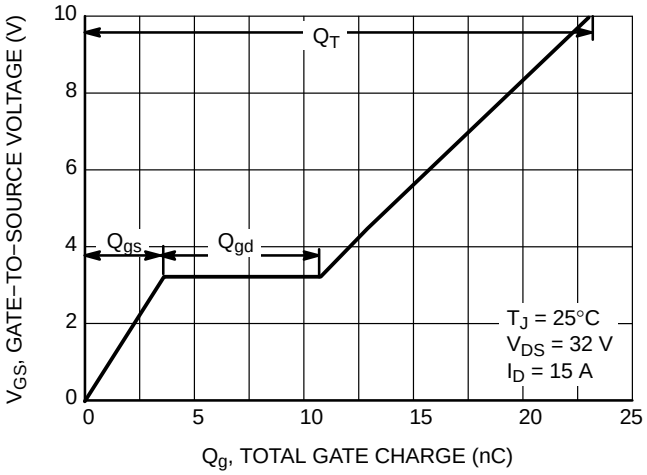



**Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge**

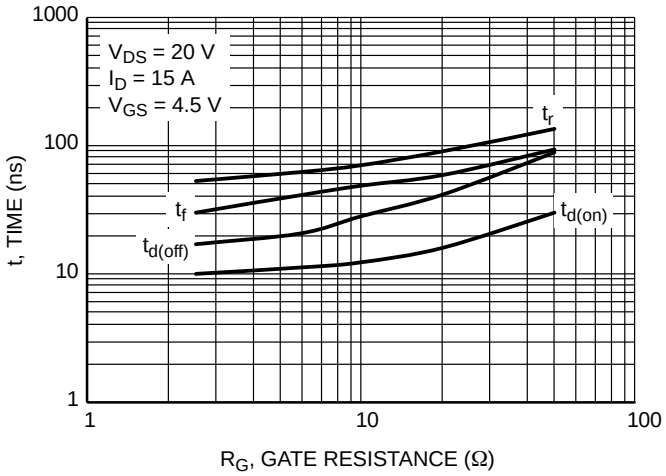



**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**

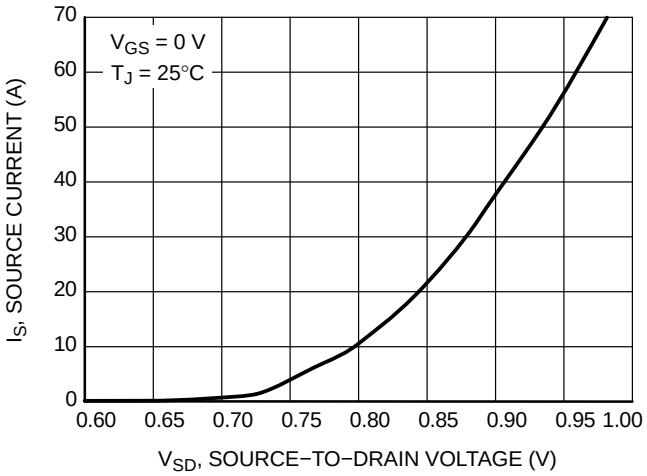



**Figure 10. Diode Forward Voltage vs. Current**

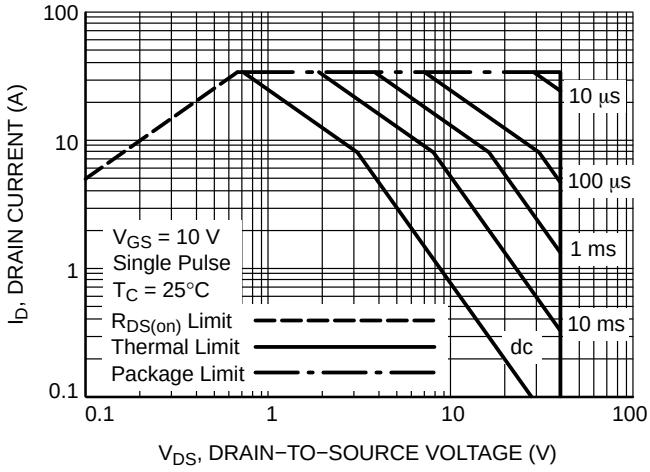



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**

## TYPICAL CHARACTERISTICS

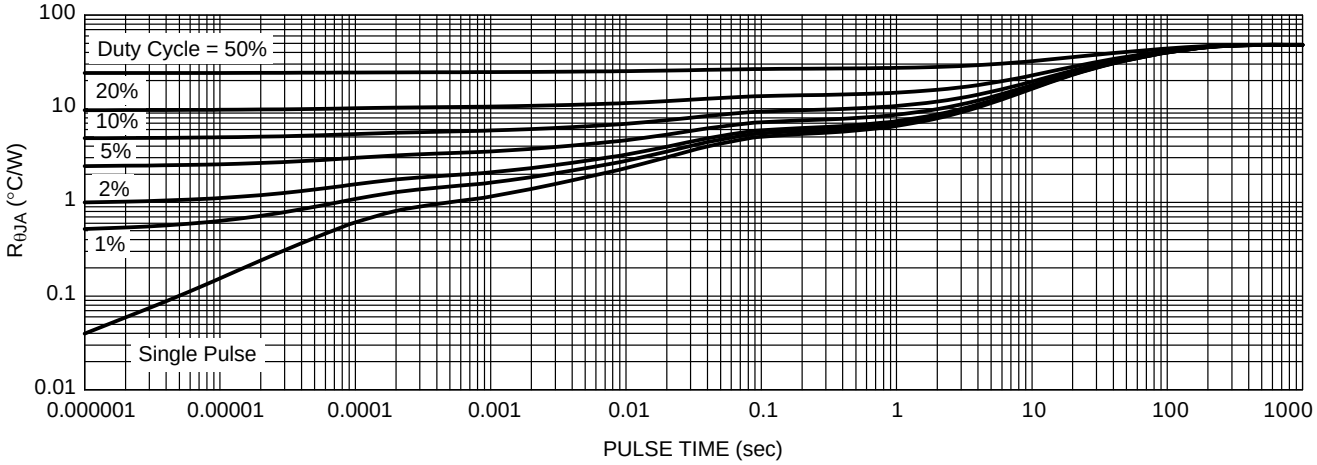
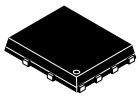



**Figure 12. Thermal Response**

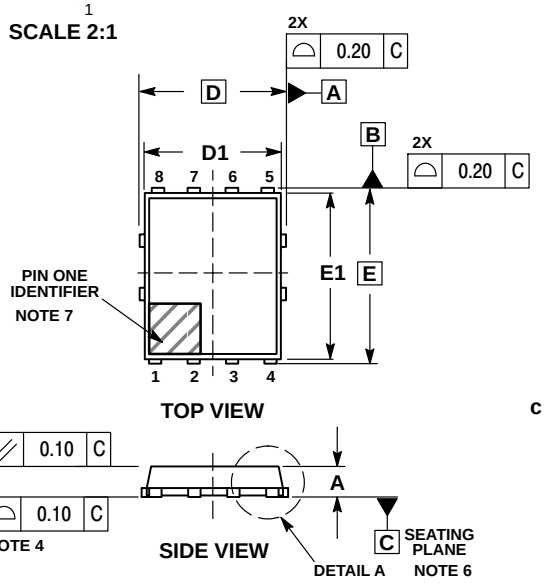
## DFN8 5x6, 1.27P Dual Flag (SO8FL−Dual)

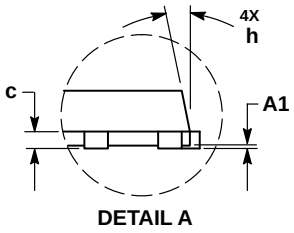
CASE 506BT
ISSUE F

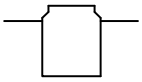
DATE 23 NOV 2021



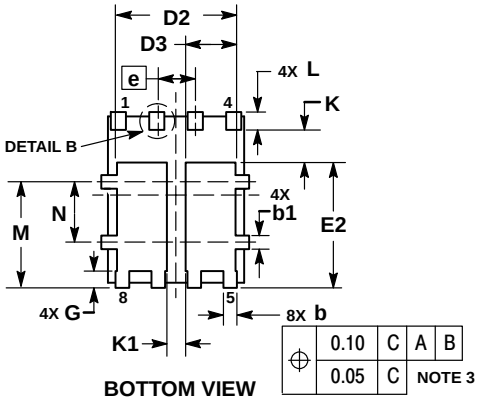
SCALE 2:1



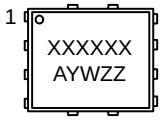
DETAIL B
ALTERNATE CONSTRUCTION




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
4. PROFILE TOLERANCE APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.
7. A VISUAL INDICATOR FOR PIN 1 MUST BE LOCATED IN THIS AREA.

| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN | NOM | MAX |
| A | 0.90 | ––– | 1.10 |
| A1 | ––– | ––– | 0.05 |
| b | 0.33 | 0.42 | 0.51 |
| b1 | 0.33 | 0.42 | 0.51 |
| c | 0.20 | ––– | 0.33 |
| D | | 5.15 BSC | |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.90 | 4.10 | 4.30 |
| D3 | 1.50 | 1.70 | 1.90 |
| E | | 6.15 BSC | |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.90 | 4.15 | 4.40 |
| e | | 1.27 BSC | |
| G | 0.45 | 0.55 | 0.65 |
| h | ––– | ––– | 12 ° |
| K | 0.51 | ––– | ––– |
| K1 | 0.56 | ––– | ––– |
| L | 0.48 | 0.61 | 0.71 |
| M | 3.25 | 3.50 | 3.75 |
| N | 1.80 | 2.00 | 2.20 |

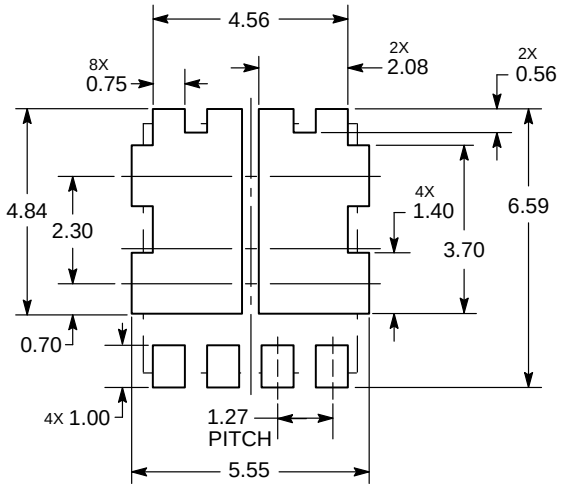
### GENERIC MARKING DIAGRAM*




XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

### SOLDERING FOOTPRINT*




DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | | |
|---|---|---|---|
| **DOCUMENT NUMBER:** | **98AON50417E** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. | |
| **DESCRIPTION:** | **DFN8 5X6, 1.27P DUAL FLAG (SO8FL−DUAL)** | | **PAGE 1 OF 1** |

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